3GPP TSG-RAN WG4 Meeting #111 draft R4-2410574

Fukuoka, Japan, May 20th – 24th, 2024

**Title:** WF on Rel-19 phase 3 NR-NTN UE RF requirements

**Agenda Item:** 10.15.4

**Source:** Qualcomm Inc.

**Document for:** Approval

## Issue 1-1 UL RB allocation for HD-FDD Refsens, both for 1Rx and 2Rx

**Agreement**: Full RB allocation.

## Issue 1-2: HD-FDD refsens for 2 Rx

**Agreement**: [0.5] dB tightening for n254 and n256, FFS for n255. n256 to be confirmed in RAN4#112.

Note: RAN4#111 maintenance agreement on n256 refsens in R4-2408787 was not considered for this agreement.

## Issue 1-3: HD-FDD refsens for 1 Rx

**Agreement:** 2.5 dB relaxation compared to 2Rx HD-FDD

## Issue 1-4: Frequency error

**Agreement:** Discuss changes common to non-Redcap NTN and (e)RedCap NTN NR UE frequency error in maintenance agenda.(e)RedCap UE frequency error requirement may be impacted by this maintenance discussion.

Option for further discussionn, not an agreement:

* As a starting point, consider (e)Redcap UE frequency error based on existing NR UE requirements.

## Issue 1-5: Maximum output power

**options for further discussion:**

Option 1: Consider increase in PC3 power level for NTN RedCap UE which only supports HD-FDD operation for a band.

Option 2: PC3 power level is the same for non-RedCap NR NTN UE and (e)RedCap NR NTN UE

## Issue 1-6: Specification structure and baseline changes

**Agreement:** Use R4-2408816 as starting point for (e)RedCap NR NTN UE RF requirements specification structure. Further changes on requirement values and additional impacted clauses (e.g. according to issue 1-4 and 1-5) as well as other improvements can be added.

FFS for suffix letter.